

In the Claims:

1. (Canceled)
2. (Currently Amended) The method of claim 4 20 wherein the photosensitive layer comprises photoresist.
3. (Original) The method of claim 2 further comprises the step of providing an antireflective coating on the substrate.
4. (Original) The method of claim 3 wherein the step of coating the substrate with a photosensitive layer comprises spin-coating techniques.
5. (Original) The method of claim 2 wherein the step of coating the substrate with a photosensitive layer comprises spin-coating techniques.
6. (Currently Amended) The method of claim 4 20 wherein the step of coating the substrate with a photosensitive layer comprises spin-coating techniques.
7. (Original) The method of claim 6 further comprises the step of providing an antireflective coating on the substrate.

8. (Currently Amended) The method of claim ~~1~~ 20 further comprises the step of providing an antireflective coating on the substrate.

9-11 (Canceled)

12. (Currently Amended) The method of claim ~~9~~ 20 wherein the vacuum environment comprises a pressure of about 1 Pa to less than 1×10^5 Pa.

13-14 (Canceled)

15. (Currently Amended) The method of claim 9 wherein the pressure is less than ~~10hPa~~ 10kPa.

16-19 (Canceled)

20. (Currently Amended) A method of pattern transfer in the fabrication of ICs, having reduced roughness on the side wall of said pattern comprising:

providing a substrate;

coating the substrate with a photosensitive layer having compounds dissolved in a solvent;

evaporating the solvent from the photosensitive layer in a vacuum environment ~~without using elevated temperatures~~ at a temperature above room temperature and less than about 70 C;

selectively exposing the photosensitive layer; and

developing the photosensitive layer to selectively remove portions thereof, ~~wherein evaporating the solvent without using elevated temperatures reduces to reduce~~ roughness on sidewalls of the photosensitive layer after development.

21. (Currently Amended) A method of pattern transfer in the fabrication of ICs, having reduced roughness on the side walls of said pattern comprising:

providing a substrate;

coating the substrate with a photoresist layer having compounds dissolved in a solvent;

evaporating the solvent from the photoresist layer in a vacuum environment ~~without using elevated temperatures~~ at a temperature above room temperature and less than about 70 C;

selectively exposing the photoresist layer; and

developing the photoresist layer to selectively remove portions thereof, ~~wherein evaporating the solvent without using elevated temperatures reduces to reduce~~ roughness on sidewalls of the photoresist layer after development.

22. (New) The method of claim 21 further comprises the step of providing an antireflective coating on the substrate.

23. (New) The method of claim 21 wherein the step of coating the substrate with a photosensitive layer comprises spin-coating techniques.

24. (New) The method of claim 21 wherein the vacuum environment comprises a pressure of about 1 Pa to less than 1×10^5 Pa.

25. (New) The method of claim 21 wherein the pressure is less than 10kPa.